

Amendments to the Specification:

Please replace the paragraph beginning at page 12, line 20 with the following amended paragraph. By this amendment, the abbreviation “ccm” at page 12, line 33, has been corrected to read “sccm.”

Referring to FIG.5, ■ corresponds to the data points shown in FIG.1 and represents the case in which the W film is deposited directly on the SiO₂ film 21A by omitting the nucleation process of FIG.3A. On the other hand, □ of FIG.5 shows the case in which the nucleation process of FIG.3A is conducted for 30 seconds under the pressure of about 67 Pa (0.5Torr) while supplying the gaseous source material containing W(CO)₆ with the flow rate of 300 SCCM. Further, △ of FIG.5 shows the case in which the nucleation process of FIG.3A is conducted under the same pressure of about 67 Pa (0.5 Torr) as in the case of □ but with the flow rate of the gaseous source material set to ~~50CCM~~ 50 SCCM. In the experiment of △, the nucleation step of FIG.3A is continued for 60 seconds.